

What is claimed is:

1. A method of forming a resist pattern comprising steps of:

5       forming a resin layer, which includes a benzophenone compound, on a substrate surface;  
          forming a photoresist layer on a surface of the resin layer;  
          forming a latent image by irradiating the  
10   photoresist layer with an exposure beam with a wavelength of 100nm to 300nm inclusive; and  
          forming a resist pattern with recessed and protruding parts in the photoresist layer by developing the photoresist layer in which the latent image has  
15   been formed.

2. A method of forming a resist pattern according to Claim 1, wherein the resin layer is formed with a thickness of 100nm to 200nm inclusive and the  
20   photoresist layer is formed with a thickness of 120nm to 200nm inclusive.

3. A method of forming a resist pattern according to Claim 2, wherein the photoresist layer is formed with a  
25   thickness of 160nm to 200nm inclusive.

4. A resist pattern forming apparatus, comprising:  
      a resin layer forming device that forms a resin layer including a benzophenone compound on a substrate  
30   surface;

      a photoresist layer forming device that forms a photoresist layer on a surface of the resin layer;  
      an exposure device that forms a latent image by

irradiating the photoresist layer with an exposure beam with a wavelength of 100nm to 300nm inclusive; and a developing device that forms a resist pattern with recessed and protruding parts in the photoresist layer  
5 by developing the photoresist layer in which the latent image has been formed.